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(54) **SEMICONDUCTOR MODULE PACKAGE**

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(58) **Field of Classification Search**

CPC H01L 23/34; H01L 2224/48137;
H01L 2224/48095; H01L 2224/49175; H01L
2924/00014

See application file for complete search history.

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(57) **ABSTRACT**

Disclosed herein is a semiconductor module package, including: a first module including a first heat radiation substrate and one or more first semiconductor elements and having a first N terminal and a first P terminal formed at one end thereof; a second module including a second heat radiation substrate and one or more second semiconductor elements, having a second N terminal and a second P terminal formed at one end thereof, and disposed so as to face the first module; and a first output terminal formed by electrically connecting the first module to the second module.

7 Claims, 3 Drawing Sheets

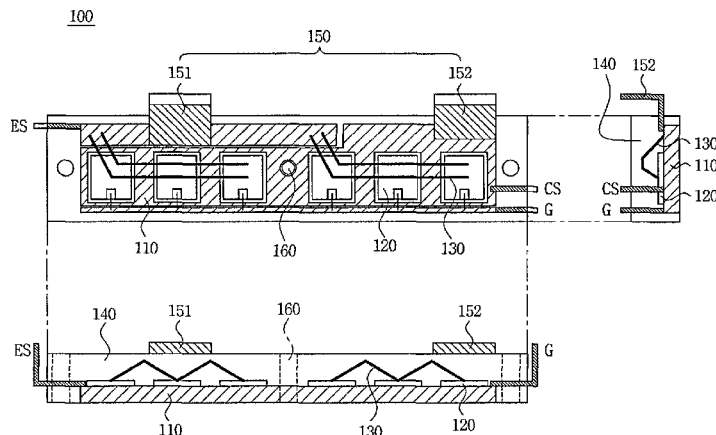


FIG. 1

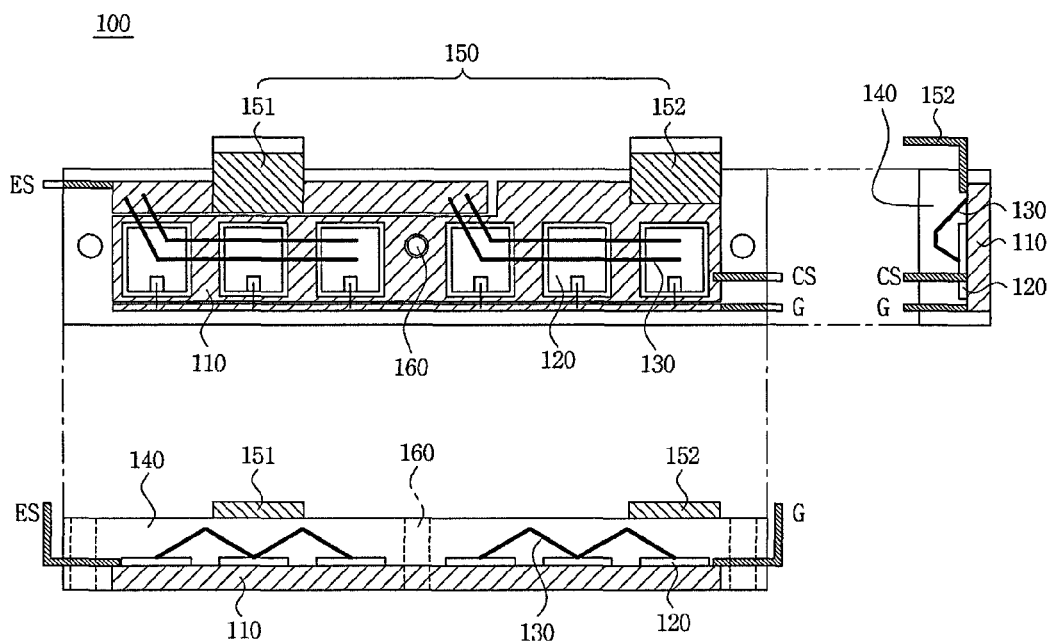


FIG. 2

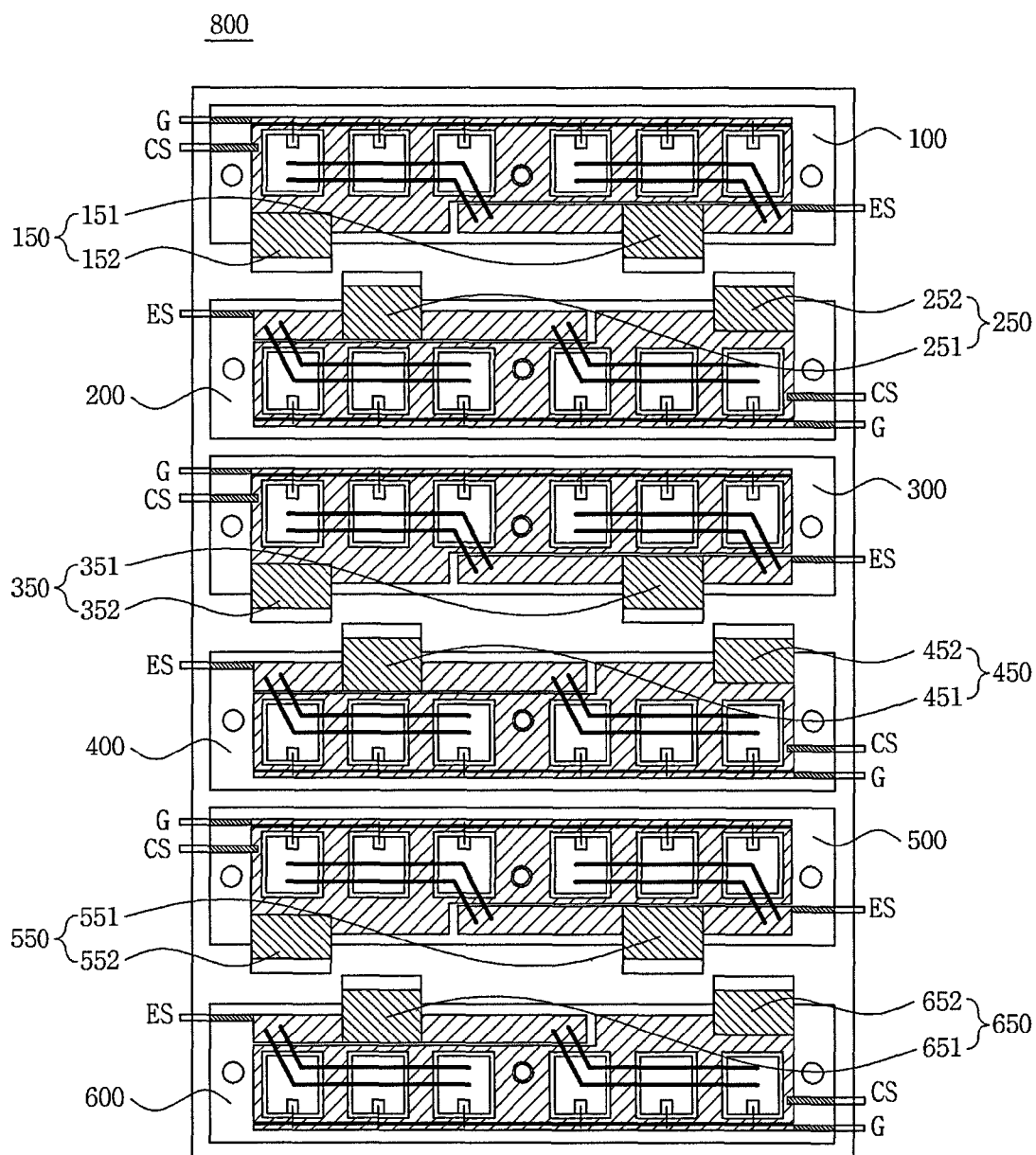
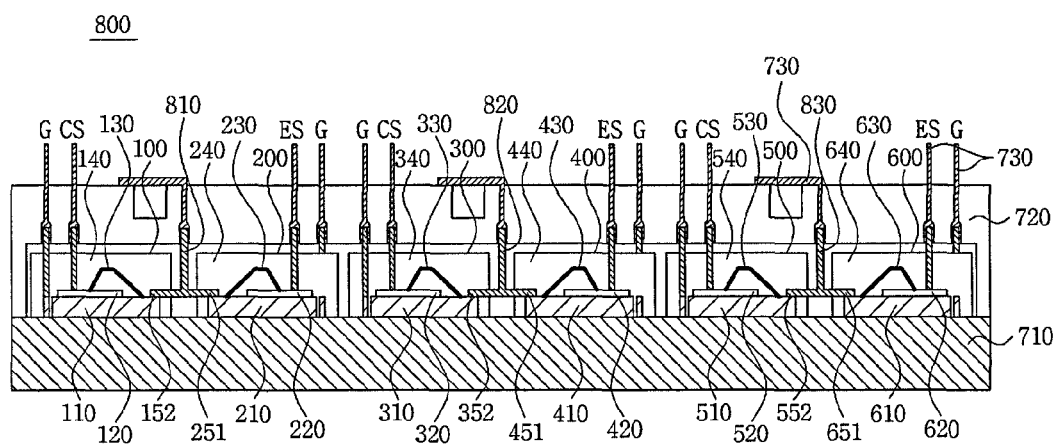


FIG. 3



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SEMICONDUCTOR MODULE PACKAGE**CROSS REFERENCE TO RELATED APPLICATION**

This application claims the benefit of Korean Patent Application No. 10-2012-0158667, filed on Dec. 31, 2012, entitled "Semiconductor Module Package", which is hereby incorporated by reference in its entirety into this application.

BACKGROUND OF THE INVENTION**1. Technical Field**

The present invention relates to a semiconductor module package.

2. Description of the Related Art

A semiconductor module package is one that a plurality of semiconductor elements are packaged into one package. Here, the semiconductor element may be a silicon controlled rectifier (SCR), a power transistor, an insulated gate bipolar transistor (IGBT), a metal oxide semiconductor (MOS) transistor, a power rectifier, a power regulator, an inverter, a converter, or like. This semiconductor module package may have one or more semiconductor elements mounted on one package (US Patent Laid-Open Publication No. 20110233608). In some cases, different types of semiconductor elements may be mounted on one package. The above-mentioned semiconductor package conventionally requires one input terminal, one N terminal, and one output terminal in order to form one phase output terminal. However, since the above-mentioned semiconductor package according to the prior art simultaneously mounts a plurality of semiconductor elements on one DBC substrate, the semiconductor package itself should be replaced once a defect occurs at one element. In addition, since the semiconductor package requires a total of three patterns for one phase module substrate, this causes a size of the module to be increased.

SUMMARY OF THE INVENTION

The present invention has been made in effort to provide a semiconductor module package capable of decreasing processing time and cost.

The present invention has been made in effort to provide a semiconductor module package capable of decreasing a size thereof.

The present invention has been made in effort to provide a semiconductor module package capable of decreasing cost caused by a defect occurrence.

According to a preferred embodiment of the present invention, there is provided a semiconductor module package, including: a first module including a first heat radiation substrate and one or more first semiconductor elements and having a first N terminal and a first P terminal formed at one end thereof; a second module including a second heat radiation substrate and one or more second semiconductor elements, having a second N terminal and a second P terminal formed at one end thereof, and disposed so as to face the first module; and a first output terminal formed by electrically connecting the first module to the second module.

The first output terminal may be formed by electrically connecting the first P terminal to the second N terminal.

The first output terminal may output at least one of W, V, and U phases.

According to another preferred embodiment of the present invention, there is provided a semiconductor module package, including: a first module including a first heat radiation

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substrate and one or more first semiconductor elements and having a first N terminal and a first P terminal formed at one end thereof; a second module including a second heat radiation substrate and one or more second semiconductor elements, having a second N terminal and a second P terminal formed at one end thereof, and disposed so as to face the first module; a third module including a third heat radiation substrate and one or more third semiconductor elements and having a third N terminal and a third P terminal formed at one end thereof; a fourth module including a fourth heat radiation substrate and one or more fourth semiconductor elements, having a fourth N terminal and a fourth P terminal formed at one end thereof, and disposed so as to face the third module; a fifth module including a fifth heat radiation substrate and one or more fifth semiconductor elements and having a fifth N terminal and a fifth P terminal formed at one end thereof; a sixth module including a sixth heat radiation substrate and one or more sixth semiconductor elements, having a sixth N terminal and a sixth P terminal formed at one end thereof, and disposed so as to face the fifth module; a first output terminal formed by electrically connecting the first module to the second module; a second output terminal formed by electrically connecting the third module to the fourth module; and a third output terminal formed by electrically connecting the fifth module to the sixth module.

The first output terminal may be formed by electrically connecting the first P terminal to the second N terminal, the second output terminal may be formed by electrically connecting the third P terminal to the fourth N terminal, and the third output terminal may be formed by electrically connecting the fifth P terminal to the sixth N terminal.

The first output terminal may output a W phase of W, V, and U phases, the second output terminal may output a V phase of W, V, and U phases, and the third output terminal may output a U phase of W, V, and U phases.

The semiconductor module package may further include a heat radiation plate formed at a lower portion of the first module to the sixth module.

The semiconductor module package may further include a housing formed so as to surround the first module to the sixth module.

The first N terminal, the second P terminal, the third N terminal, the fourth P terminal, the fifth N terminal, the sixth P terminal, the first output terminal, the second output terminal, and the third output terminal may be formed so as to be protruded to the outside while penetrating through the housing.

The semiconductor module package may further include a housing terminal having one end contacting at least one of the first N terminal, the second P terminal, the third N terminal, the fourth P terminal, the fifth N terminal, the sixth P terminal, the first output terminal, the second output terminal, and the third output terminal, and the other end formed so as to be protruded to the outside while penetrating through the housing.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other objects, features and advantages of the present invention will be more clearly understood from the following detailed description taken in conjunction with the accompanying drawings, in which:

FIG. 1 is an exemplary view of a first module according to a preferred embodiment of the present invention;

FIG. 2 is an exemplary view of a semiconductor module package according to the preferred embodiment of the present invention; and

FIG. 3 is an exemplary view showing a side view of the semiconductor module package according to the preferred embodiment of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

The objects, features and advantages of the present invention will be more clearly understood from the following detailed description of the preferred embodiments taken in conjunction with the accompanying drawings. Throughout the accompanying drawings, the same reference numerals are used to designate the same or similar components, and redundant descriptions thereof are omitted. Further, in the following description, the terms "first", "second", "one side", "the other side" and the like are used to differentiate a certain component from other components, but the configuration of such components should not be construed to be limited by the terms. Further, in the description of the present invention, when it is determined that the detailed description of the related art would obscure the gist of the present invention, the description thereof will be omitted.

Hereinafter, preferred embodiments of the present invention will be described in detail with reference to the attached drawings.

FIG. 1 is an exemplary view of a first module according to a preferred embodiment of the present invention.

Referring to FIG. 1, the first module **100** may include a first heat radiation substrate **110**, a first semiconductor element **120**, a first connection member **130**, a first molding part **140**, and the first terminal **150**.

The first heat radiation substrate **110** may radiate heat generated from the first semiconductor element **120** to the outside. The first heat radiation substrate **110** may be made of a heat conductive material. For example, the first heat radiation substrate **110** may be formed to include copper or aluminum. Alternatively, the first heat radiation substrate **110** may be a direct bonding copper (DBC) substrate.

The first semiconductor element **120** may be formed on the first heat radiation substrate **110**. One or more first semiconductor elements **120** may be formed. According to the preferred embodiment of the present invention, the first module **100** may include six first semiconductor elements **120**. As the first semiconductor element **120**, a silicon controlled rectifier (SCR), a power transistor, an insulated gate bipolar transistor (IGBT), a metal oxide semiconductor (MOS) transistor, a power rectifier, a power regulator, an inverter, a converter, or a high power semiconductor chip or diode formed of a combination thereof may be used.

Although not shown in the preferred embodiment of the present invention, an insulating layer (not shown) may be formed between the first heat radiation substrate **110** and the first semiconductor element **120**.

The first connection member **130** may be formed so as to electrically connect between the first semiconductor elements **120**. Alternatively, although not shown, the first connection member **130** may electrically connect the first semiconductor elements **120** to a circuit pattern (not shown) formed on the first heat radiation substrate **110**. The first connection member **130** may be formed of an electrical conductive material such as copper. For example, the first connection member **130** may be a wire or a lead frame.

The first molding part **140** may be formed so as to protect the first semiconductor element **120** and the first connection member **130** from an external environment. The first molding part **140** may be formed so as to surround the first semiconductor element **120** and the first connection member **130**. For

example, the first molding part **140** may be formed of an epoxy molding compound (EMC).

The first terminal **150** may connect between an inside and the outside of the first module **100**. The first terminal **150** may be formed of a first N terminal **151** and a first P terminal **152**.

The first N terminal **151** may be a terminal applying external power to the first module **100**. The first N terminal **151** may apply external power to the first semiconductor element **120**. The first P terminal **152** may be a terminal capable of applying output voltage of the first module **100** to the outside.

The first terminal **150** formed as described above has one end electrically connected to the first semiconductor element **120** or the circuit pattern (not shown) of the first heat radiation substrate **100**, and the other end protruded to the outside of the first molding part **140**.

In addition, according to the preferred embodiment of the present invention, the first module **100** may be provided with a connecting hole **160** for connecting with a heat radiation plate (**710** of FIG. 3). However, the connecting hole **160** is to screw-connect with the heat radiation plate (**710** of FIG. 3) and the connecting hole **160** is a configuration part which may be removed when the heat radiation plate (**710** of FIG. 3) and the first module **100** are adhered by an adhesive member. As the adhesive member, an adhesive material of a heat conductive material may be used. Alternatively, low temperature firing materials such as solder, a silver (Ag) paste, a copper paste, and the like may be used.

Although not described in the preferred embodiment of the present invention, it is generally obvious to those skilled in the art that a sensor terminal and a gate terminal applied to the module including the semiconductor element may be further formed. Therefore, a description thereof will be omitted.

Although the preferred embodiment of the present invention illustrates only the first module, the above-mentioned configuration may also be applied to a second module (**200** of FIG. 3) to a sixth module (**600** of FIG. 3). That is, the second module (**200** of FIG. 3) to the sixth module (**600** of FIG. 3) configuring the semiconductor module package according to the preferred embodiment of the present invention may be formed of the same structure as the first module **100**.

FIG. 2 is an exemplary view of a semiconductor module package according to the preferred embodiment of the present invention.

Referring to FIG. 2, an arrangement of the first module **100** to the sixth module **600** configuring a semiconductor module package **800** may be seen.

The semiconductor module package **800** may include the first module **100** to the sixth module **600**. In this configuration, a first output terminal (**810** of FIG. 3) may be formed from the first module **100** and a second module **200**. In addition, a second output terminal (**820** of FIG. 3) may be formed from a third module **300** and a fourth module **400**. In addition, a third output terminal (**830** of FIG. 3) may be formed from a fifth module **500** and a sixth module **600**.

The first module **100** and the second module **200** may be disposed so as to face each other. That is, the second module **200** may be disposed in a form in which the first module **100** is rotated by 180°. By the arrangement as described above, a first P terminal **152** of the first module **100** and a second N terminal **251** of the second module **200** may be disposed adjacent to each other. Although not shown in the present invention, the first P terminal **152** and the second N terminal **251** adjacent to each other may be electrically connected to each other. Therefore, a signal input from a second P terminal **252** may be input to the first P terminal **152** through the second N terminal **251**. That is, when the signal is input to the second module **200**, the signal may be transmitted to the first

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module **100** through the second module **200**. The first output terminal (**810** of FIG. **3**) may be formed at the first P terminal **152** and the second N terminal **251** as described above. In this configuration, the first output terminal (**810** of FIG. **3**) may be an output terminal outputting a W phase among three phases (W, V, U). According to the preferred embodiment of the present invention, the second module **200** is disposed so as to face the first module **100**, such that the W phase may be output using one input and one output.

The third module **300** and the fourth module **400** may be disposed so as to face each other. That is, the fourth module **400** may be disposed in a form in which the third module **300** is rotated by 180°. By the arrangement as described above, a third P terminal **352** of the third module **300** and a fourth N terminal **451** of the fourth module **400** may be disposed adjacent to each other. Although not shown in the present invention, the third P terminal **352** and the fourth N terminal **451** adjacent to each other may be electrically connected to each other. Therefore, a signal input from a fourth P terminal **452** may be input to the third P terminal **352** through the fourth N terminal **451**. That is, when the signal is input to the fourth module **400**, the signal may be transmitted to the third module **300** through the fourth module **400**. The second output terminal (**820** of FIG. **3**) may be formed at the third P terminal **352** and the fourth N terminal **451** as described above. In this configuration, the second output terminal (**820** of FIG. **3**) may be an output terminal outputting a V phase among three phases (W, V, U). According to the preferred embodiment of the present invention, the fourth module **400** is disposed so as to face the third module **300**, such that the V phase may be output using one input and one output.

The fifth module **500** and the sixth module **600** may be disposed so as to face each other. That is, the sixth module **600** may be disposed in a form in which the fifth module **500** is rotated by 180°. By the arrangement as described above, a fifth P terminal **552** of the fifth module **500** and a sixth N terminal **651** of the sixth module **600** may be disposed adjacent to each other. Although not shown in the present invention, the third P terminal **552** and the fourth N terminal **651** adjacent to each other may be electrically connected to each other. Therefore, a signal input from a sixth P terminal **652** may be input to the fifth P terminal **552** through the sixth N terminal **651**. That is, when the signal is input to the sixth module **600**, the signal may be transmitted to the fifth module **500** through the sixth module **600**. The third output terminal (**830** of FIG. **3**) may be formed at the fifth P terminal **552** and the sixth N terminal **651** as described above. In this configuration, the third output terminal (**830** of FIG. **3**) may be an output terminal outputting a U phase among three phases (W, V, U). According to the preferred embodiment of the present invention, the sixth module **600** is disposed so as to face the fifth module **500**, such that the U phase may be output using one input and one output.

FIG. **3** is an exemplary view showing a side view of the semiconductor module package according to the preferred embodiment of the present invention.

Referring to FIG. **3**, the semiconductor module package **800** may include the first module **100** to the sixth module **600**, a heat radiation plate **710**, a housing **720**, and a housing terminal **730**.

In the preferred embodiment of the present invention, since both of the first module **100** and the sixth module **600** are configured of the same configuration parts as those described in FIG. **1**, the respective modules are briefly described and a detail description thereof is referred to FIG. **1**.

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The first module **100** may include the first heat radiation substrate **110**, the first semiconductor element **120**, the first connection member **130**, the first molding part **140**, and the first terminal (**150** of FIG. **2**).

The first heat radiation substrate **110** may radiate heat generated from the first semiconductor element **120** to the outside. The first heat radiation substrate **110** may be made of a heat conductive material. The first semiconductor element **120** may be formed on the first heat radiation substrate **110**. One or more first semiconductor elements **120** may be formed. The first connection member **130** may be formed so as to electrically connect between the first semiconductor element **120** and a circuit pattern (not shown). The first connection member **130** may be formed of a wire or a lead frame. The first molding part **140** may be formed so as to protect the first semiconductor element **120** and the first connection member **130**. The first molding part **140** may be formed of an epoxy molding compound. The first terminal (**150** of FIG. **2**) may be a terminal connecting between an inside and the outside of the first module **100**. The first terminal (**150** of FIG. **2**) may include the first N terminal (**151** of FIG. **2**) and the first P terminal **152**.

The second module **200** may include a second heat radiation substrate **210**, a second semiconductor element **220**, a second connection member **230**, a second molding part **240**, and a second terminal (**250** of FIG. **2**). The second terminal (**250** of FIG. **2**) may be a terminal connecting between an inside and the outside of the second module **200**. The second terminal (**250** of FIG. **2**) may include the second N terminal **251** and the second P terminal **252**.

In this configuration, the first module **100** and the second module **200** may be disposed so as to face each other. Therefore, the first P terminal **152** of the first module **100** and the second N terminal **251** of the second module **200** may be disposed so as to face each other. In addition, the first P terminal **152** and the second N terminal **251** may be electrically connected to each other without an additional circuit pattern. In this case, the first P terminal **152** and the second N terminal **251** may directly contact the outside of the first module **110** and the second module **200**, or may be electrically connected to each other by being connected by the electrical conductive material. As described above, the first P terminal **152** and the second N terminal **251** may be electrically connected to each other so as to form the first output terminal **810**. Here, the first output terminal **810** may output the W phase.

The third module **300** may include a third heat radiation substrate **310**, a third semiconductor element **320**, a third connection member **330**, a third molding part **340**, and a third terminal (**350** of FIG. **2**). The third terminal (**350** of FIG. **2**) may be a terminal connecting between an inside and the outside of the third module **300**. The third terminal (**350** of FIG. **2**) may include a third N terminal (**351** of FIG. **2**) and a third P terminal **352**.

The fourth module **400** may include a fourth heat radiation substrate **410**, a fourth semiconductor element **420**, a fourth connection member **430**, a fourth molding part **440**, and a fourth terminal (**450** of FIG. **2**). The fourth terminal (**450** of FIG. **2**) may be a terminal connecting between an inside and the outside of the fourth module **400**. The fourth terminal (**450** of FIG. **2**) may include a fourth N terminal **451** and a first P terminal (**452** of FIG. **2**).

In this configuration, the third module **300** and the fourth module **400** may be disposed so as to face each other. Therefore, the third P terminal **352** of the third module **300** and the fourth N terminal **451** of the fourth module **400** may be disposed so as to face each other. In addition, the third P

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terminal 352 and the fourth N terminal 451 may be electrically connected to each other without an additional circuit pattern. In this case, the third P terminal 352 and the fourth N terminal 451 may directly contact the outside of the third module 300 and the fourth module 400, or may be electrically connected to each other by being connected by the electrical conductive material. As described above, the third P terminal 352 and the fourth N terminal 451 may be electrically connected to each other so as to form the second output terminal 820. Here, the second output terminal 820 may output the V phase.

The fifth module 500 may include a fifth heat radiation substrate 510, a fifth semiconductor element 520, a fifth connection member 530, a fifth molding part 540, and a fifth terminal (550 of FIG. 2). The fifth terminal (550 of FIG. 2) may be a terminal connecting between an inside and the outside of the fifth module 500. The fifth terminal (550 of FIG. 2) may include a fifth N terminal (551 of FIG. 2) and a fifth P terminal 552.

The sixth module 600 may include a sixth heat radiation substrate 610, a sixth semiconductor element 620, a sixth connection member 630, a sixth molding part 640, and a sixth terminal (650 of FIG. 2). The sixth terminal (650 of FIG. 2) may be a terminal connecting between an inside and the outside of the sixth module 600. The sixth terminal (650 of FIG. 2) may include a sixth N terminal 651 and a sixth P terminal (652 of FIG. 2).

In this configuration, the fifth module 500 and the sixth module 600 may be disposed so as to face each other. Therefore, the fifth P terminal 552 of the fifth module 500 and the sixth N terminal 651 of the sixth module 600 may be disposed so as to face each other. In addition, the fifth P terminal 552 and the sixth N terminal 651 may be electrically connected to each other without an additional circuit pattern. In this case, the fifth P terminal 552 and the sixth N terminal 651 may directly contact the outside of the fifth module 500 and the sixth module 600, or may be electrically connected to each other by being connected by the electrical conductive material. As described above, the fifth P terminal 552 and the sixth N terminal 651 may be electrically connected to each other so as to form the third output terminal 830. Here, the third output terminal 830 may output the U phase.

Each of the first module 100 to the sixth module 600 formed as described above may be separately packaged.

The heat radiation plate 710 may be formed at a lower portion of the first module 100 and the second module 200. The heat radiation plate 710 may be formed so as to radiate heat generated from the first module 100 to the sixth module 600 to the outside. The heat radiation plate 710 may be formed of the heat conductive material. For example, the heat radiation plate 710 may be a heat sink. Here, the heat radiation plate 710 and the first module 100 to the sixth module 600 may be each connected to each other by a screw. Alternatively, the heat radiation plate 710 and the first module 100 to the sixth module 600 may be adhered to each other using a low temperature firing material such as a solder, a silver (Ag) paste, a copper (Cu) paste, or the like.

The housing 720 may be formed so as to protect the first module 100 to the sixth module 600 from the external environment. The housing 720 is formed on the heat radiation plate 710 so as to surround the first module 100 to the sixth module 600. The housing 720 formed as described above may be coupled to the heat radiation plate 710. For example, the housing 720 and the heat radiation plate 710 may be con-

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nected to each other by the screw. Alternatively, the housing 720 and the heat radiation plate 710 may be adhered to each other by applying the adhesive material of the heat conductive material. Although FIG. 3 shows a case in which the housing 720 is formed on the heat radiation plate 710, the present invention is not limited thereto. That is, the housing 720 may be formed so as to surround all configuration parts including the heat radiation plate 710. According to the prior art, the housing 720 is filled with a molding material such as an epoxy molding compound, a silicone gel, or the like, but the present invention does not necessarily require this configuration part. The reason is that the first module 100 to the sixth module 600 are separately molded. Therefore, whether or not the housing 720 is filled with the molding material may be performed by a selection of those skilled in the art.

That is, the housing terminal 730 may be formed so as to have the other end thereof protruded to the outside while penetrating through the housing 720. In addition, the housing terminal 730 may have one end thereof capable of being connected to any of all input and output terminals of the first module 100 to the sixth module 600. For example, the housing terminal 730 may be connected to the first N terminal 151, the second P terminal 252, the third N terminal 351, the fourth P terminal 452, the fifth N terminal 551, the sixth P terminal 652, the first output terminal 810, the second output terminal 820, and the third output terminal 830, respectively. In addition, the housing terminal 730 may be connected to other terminals of the first module 100 to the sixth module 600. The housing terminal 730 formed as described above may be formed so as to electrically connect the first module 100 to the sixth module 600 to the outside of the housing 720.

Although the preferred embodiment of the present invention shows a case in which the housing terminal 730 is formed so as to electrically connect the first module 100 to the sixth module 600 to the outside of the housing 720, the present invention is not limited thereto. That is, in the case in which the input and output terminals of the first module 100 to the sixth module 600 are formed so as to be long enough to be protruded to the outside of the housing 720, the housing terminal 730 may be omitted.

According to the preferred embodiment of the present invention, the semiconductor module package requiring only three input and output terminals may be implemented by disposing the same module rotated by 180°, as compared to the prior art in which four input and output terminals are required. Therefore, the circuit pattern for forming the input and output terminals may be decreased. Therefore, the size of the semiconductor module package may be decreased, the processes may be simplified, and the processing cost may be saved. In addition, the semiconductor module package according to the preferred embodiment of the present invention separately molds the respective modules, such that when the defect is generated, only the module having the defect is exchanged, thereby making it possible to save cost.

The semiconductor module package according to the preferred embodiment of the present invention may decrease processing time and cost.

The semiconductor module package according to the preferred embodiment of the present invention may decrease the size thereof.

The semiconductor module package according to the preferred embodiment of the present invention may decrease the cost caused by the defect occurrence.

Although the embodiments of the present invention have been disclosed for illustrative purposes, it will be appreciated that the present invention is not limited thereto, and those skilled in the art will appreciate that various modifications,

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additions and substitutions are possible, without departing from the scope and spirit of the invention.

Accordingly, any and all modifications, variations or equivalent arrangements should be considered to be within the scope of the invention, and the detailed scope of the invention will be disclosed by the accompanying claims.

What is claimed is:

1. A semiconductor module package, comprising:

a first module including a first heat radiation substrate and one or more first semiconductor elements and having a first N terminal and a first P terminal formed at one end thereof;

a second module including a second heat radiation substrate and one or more second semiconductor elements, having a second N terminal and a second P terminal formed at one end thereof, and disposed so as to face the first module;

a third module including a third heat radiation substrate and one or more third semiconductor elements and having a third N terminal and a third P terminal formed at one end thereof;

a fourth module including a fourth heat radiation substrate and one or more fourth semiconductor elements, having a fourth N terminal and a fourth P terminal formed at one end thereof, and disposed so as to face the third module;

a fifth module including a fifth heat radiation substrate and one or more fifth semiconductor elements and having a fifth N terminal and a fifth P terminal formed at one end thereof;

a sixth module including a sixth heat radiation substrate and one or more sixth semiconductor elements, having a sixth N terminal and a sixth P terminal formed at one end thereof, and disposed so as to face the fifth module;

a first output terminal formed by electrically connecting the first module to the second module;

a second output terminal formed by electrically connecting the third module to the fourth module; and

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a third output terminal formed by electrically connecting the fifth module to the sixth module.

2. The semiconductor module package as set forth in claim 1, wherein the first output terminal is formed by electrically connecting the first P terminal to the second N terminal, the second output terminal is formed by electrically connecting the third P terminal to the fourth N terminal, and the third output terminal is formed by electrically connecting the fifth P terminal to the sixth N terminal.

3. The semiconductor module package as set forth in claim 1, wherein the first output terminal outputs a W phase of W, V, and U phases, the second output terminal outputs a V phase of W, V, and U phases, and the third output terminal outputs a U phase of W, V, and U phases.

4. The semiconductor module package as set forth in claim 1, further comprising a heat radiation plate formed at a lower portion of the first module to the sixth module.

5. The semiconductor module package as set forth in claim 1, further comprising a housing formed so as to surround the first module to the sixth module.

6. The semiconductor module package as set forth in claim 5, wherein the first N terminal, the second P terminal, the third N terminal, the fourth P terminal, the fifth N terminal, the sixth P terminal, the first output terminal, the second output terminal, and the third output terminal are formed so as to be protruded to the outside while penetrating through the housing.

7. The semiconductor module package as set forth in claim 6, further comprising a housing terminal having one end contacting at least one of the first N terminal, the second P terminal, the third N terminal, the fourth P terminal, the fifth N terminal, the sixth P terminal, the first output terminal, the second output terminal, and the third output terminal, and the other end formed so as to be protruded to the outside while penetrating through the housing.

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